

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240416US0DIV	SERIAL NO. 10/618,085
LIST OF REFERENCES CITED BY APPLICANT <i>O I P E</i> FEB 01 2005 P A T E N T & T R A D E M A R K S O U R C E		APPLICANT Masakazu KANECHIKA, et al.			
		FILING DATE July 14, 2003		GROUP 2813	
		U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS
	AA				
	AB				
	AC				
	AD				
	AE				
	AF				
	AG				
	AH				
	AI				
	AJ				
	AK				
	AL				
	AM				
	AN				
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
	AO	JP8-306752	11-22-96	JAPAN (with English Abstract)	
	AP	JP7-118100	05-09-95	JAPAN (with English Abstract)	
	AQ	JP8-203863	08-09-96	JAPAN (with English Abstract)	
	AR	JP9-232482	09-05-97	JAPAN (with English Abstract)	
	AS				
	AT				
	AU				
	AV				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)					
	AW	Hayakawa et al; "Mechanism of Residue Formation in Silicon Trench Etching Using a Bromine-Based Plasma," Jpn. J. Appl. Phys., Vol. 37 (1998) pp. 5-9.			
	AX				
	AY				
	AZ			<input type="checkbox"/> Additional References sheet(s) attached	
Examiner				Date Considered	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

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